

1. General description

Planar passivated sensitive gate four quadrant triac in a SOT78 plastic package intended for use in general purpose bidirectional switching and phase control applications. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Low holding current for low current loads and lowest EMI at commutation
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- Triggering in all four quadrants

3. Applications

- General purpose motor control
- General purpose switching

4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DRM}	repetitive peak off- state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 20 \text{ ms}; \frac{\text{Fig. 4}}{25}; \frac{1}{25}; \frac{1}{2$	-	-	25	A
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 107 \text{ °C}$; Fig. 1; Fig. 2; Fig. 3	-	-	4	A
Static chara	cteristics	· · · · · ·	L L			
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	-	2.5	10	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	-	4	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	-	5	10	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 7</u>	-	11	25	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	2.2	15	mA

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2-71
2	T2	main terminal 2		sym051
3	G	gate		
mb	T2	mounting base; main terminal 2		
			TO-220AB (SOT78)	

6. Ordering information

Table 3. Ordering in	formation				
Type number	Package				
	Name	Description	Version		
BT136-800E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78		

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7. Limiting values

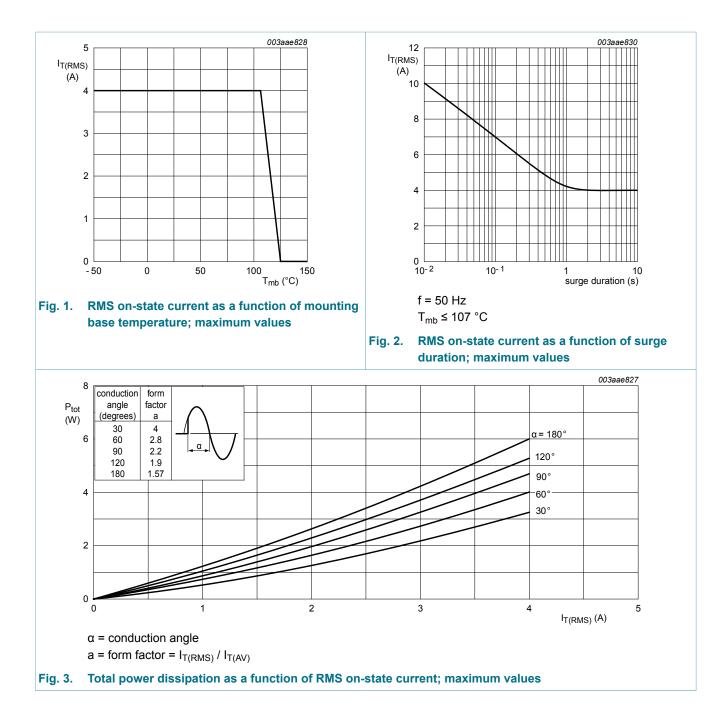
Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 107 \text{ °C}$; Fig. 1; Fig. 2; Fig. 3	-	4	A
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; <u>Fig. 4</u> ; <u>Fig. 5</u>	-	25	A
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	27	A
l ² t	I2t for fusing	t _p = 10 ms; SIN	-	3.1	A ² s
dl _T /dt	rate of rise of on-state current	$I_T = 6 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A}/\mu\text{s};$ T2+ G+	-	50	A/µs
		$I_T = 6 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A}/\mu\text{s};$ T2+ G-	-	50	A/µs
		$I_T = 6 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A}/\mu\text{s};$ T2- G-	-	50	A/µs
		$I_T = 6 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A}/\mu\text{s};$ T2- G+	-	10	A/µs
I _{GM}	peak gate current		-	2	А
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

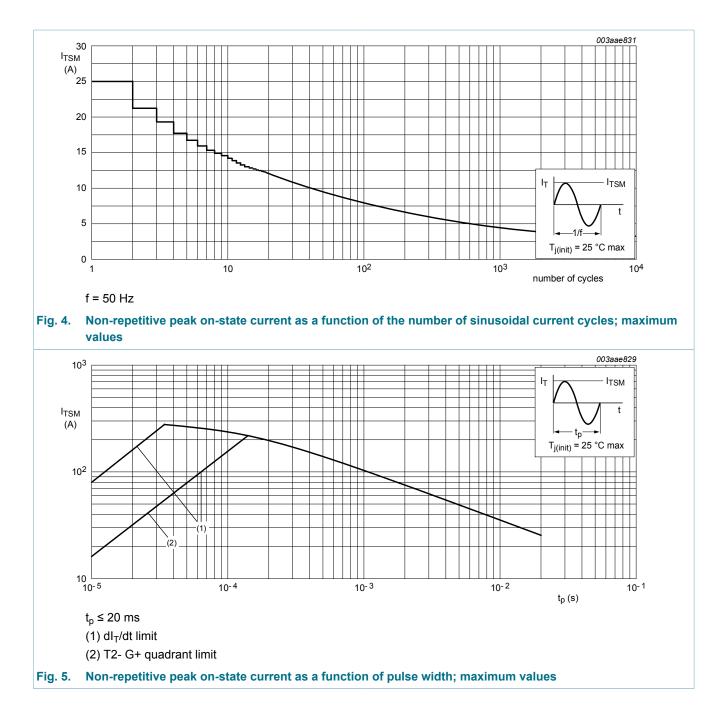
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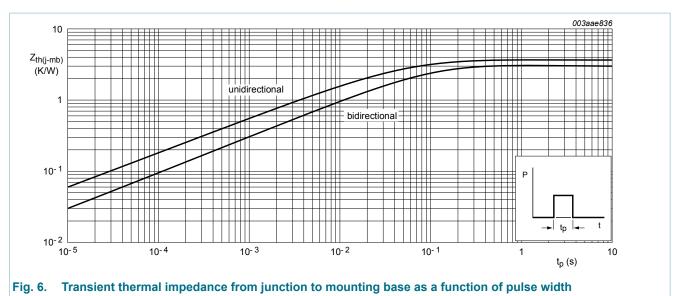
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8. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance	half cycle; <u>Fig. 6</u>	-	-	3.7	K/W
	from junction to mounting base	full cycle; <u>Fig. 6</u>	-	-	3	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



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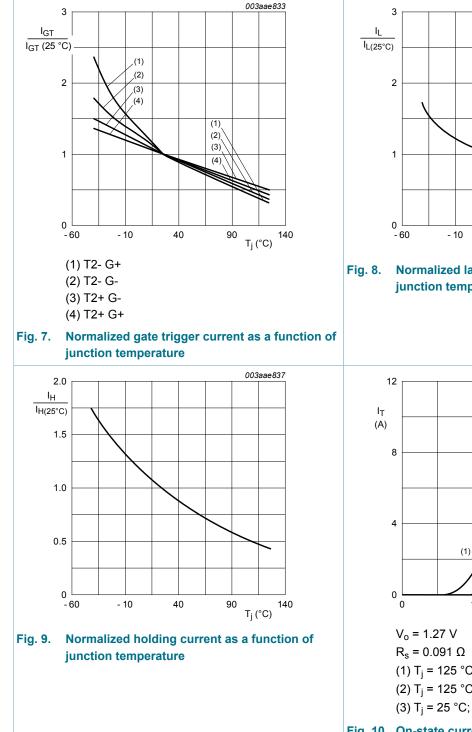
9. Characteristics

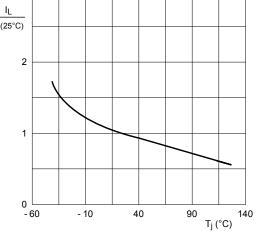
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I _{GT}	gate trigger current	V_D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	-	2.5	10	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	-	4	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	-	5	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 7</u>	-	11	25	mA
ΙL	latching current	V_D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 8</u>	-	3	15	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G-};$ T _j = 25 °C; Fig. 8	-	10	20	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G-};$ T _j = 25 °C; Fig. 8	-	2.5	15	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G+};$ T _j = 25 °C; Fig. 8	-	4	20	mA
н	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	2.2	15	mA
VT	on-state voltage	I _T = 5 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.4	1.7	V
√ _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic cl	naracteristics	· · · · · · · · · · · · · · · · · · ·				
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	-	50	-	V/µs
lgt	gate-controlled turn-on time	I _{TM} = 6 A; V _D = 800 V; I _G = 0.1 A; dI _G / dt = 5 A/µs	-	2	-	μs

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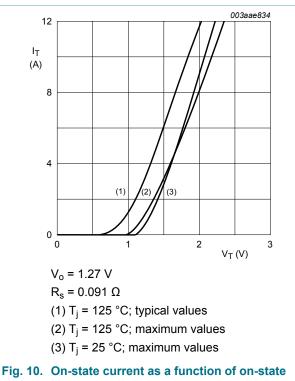
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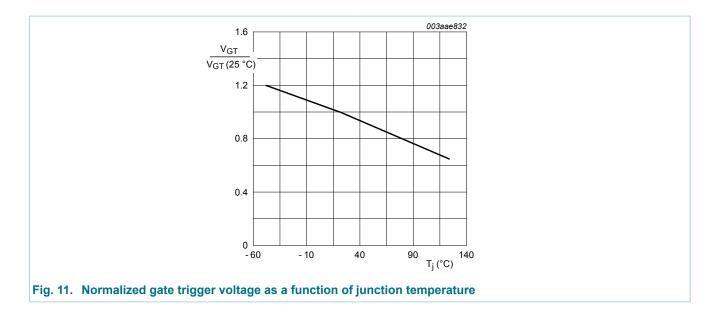




voltage

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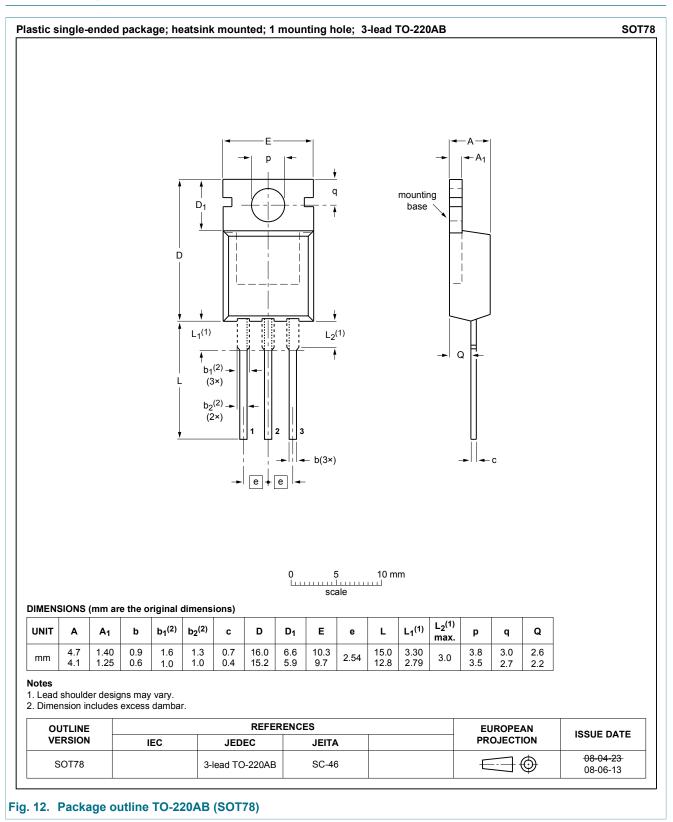
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10. Package outline



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11. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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